



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

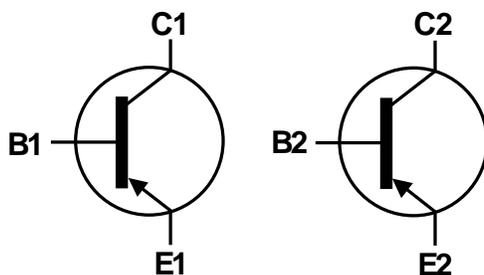
- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

Mechanical Data

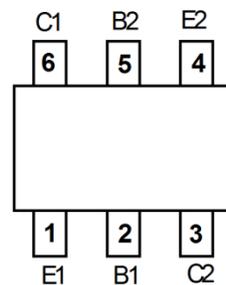
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

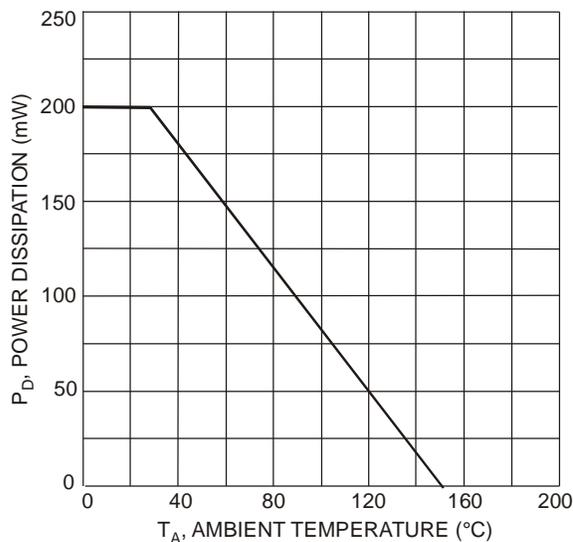


Figure 1 Power Derating Curve

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	—	V	$I_C = -10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 7)	BV_{CEO}	-60	—	—	V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}	—	—	-10	nA	$V_{CB} = -50\text{V}, I_E = 0$
Collector Cutoff Current	I_{CEX}	—	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
Base Cutoff Current	I_{BL}	—	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h_{FE}	75	—	—	—	$I_C = -100\mu\text{A}, V_{CE} = -10\text{V}$
		100	—	—		$I_C = -1.0\text{mA}, V_{CE} = -10\text{V}$
		100	—	—		$I_C = -10\text{mA}, V_{CE} = -10\text{V}$
		100	—	300		$I_C = -150\text{mA}, V_{CE} = -10\text{V}$
		50	—	—		$I_C = -500\text{mA}, V_{CE} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	-0.4 -1.6	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	—	-1.3 -2.6	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{OBO}	—	—	8.0	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{IBO}	—	—	30	pF	$V_{EB} = -2.0\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain Bandwidth Product	f_T	200	—	—	MHz	$V_{CE} = -20\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS						
Turn-On Time	t_{off}	—	—	45	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$
Delay Time	t_d	—	—	10	ns	
Rise Time	t_r	—	—	40	ns	
Turn-Off Time	t_{off}	—	—	100	ns	$V_{CC} = -6\text{V}, I_C = -150\text{mA}, I_{B1} = -I_{B2} = -15\text{mA}$
Storage Time	t_s	—	—	80	ns	
Fall Time	t_f	—	—	30	ns	

Note: 7. Short duration pulse test used to minimize self-heating effect.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

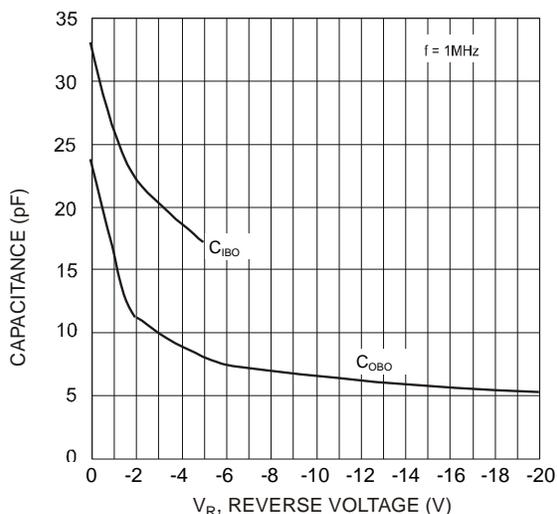


Fig. 2. Typical Capacitance Characteristics

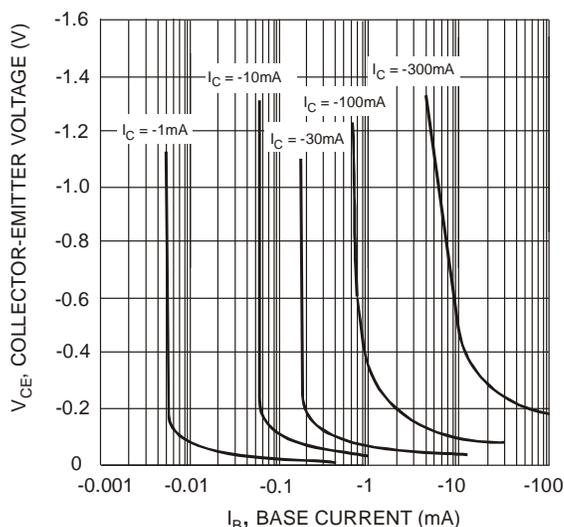


Fig. 3. Typical Collector Saturation Region

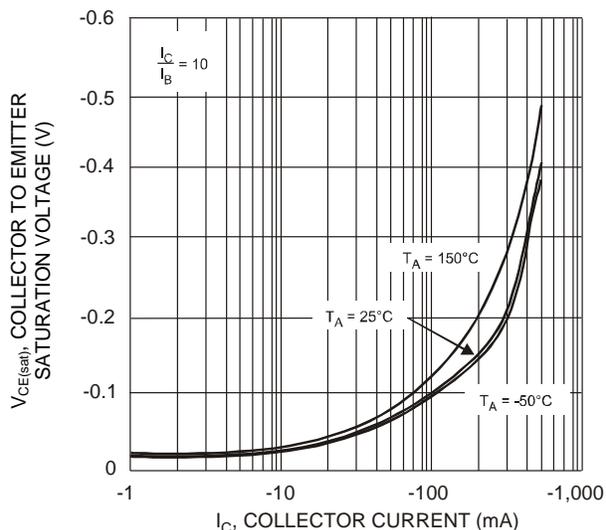


Fig. 4. Collector Emitter Saturation Voltage vs. Collector Current

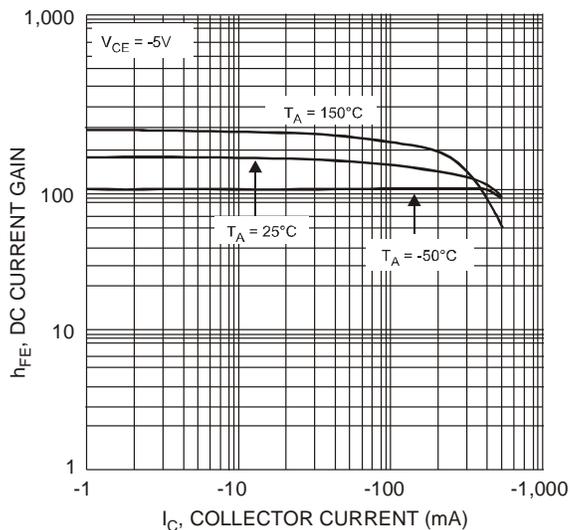


Fig. 5. DC Current Gain vs. Collector Current

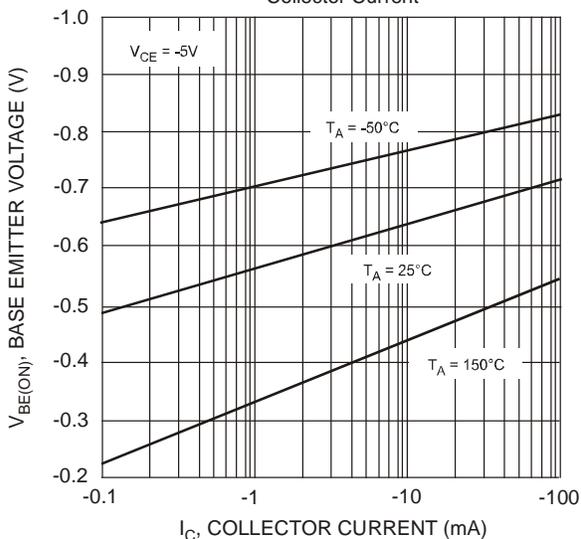


Fig. 6. Base Emitter Voltage vs. Collector Current

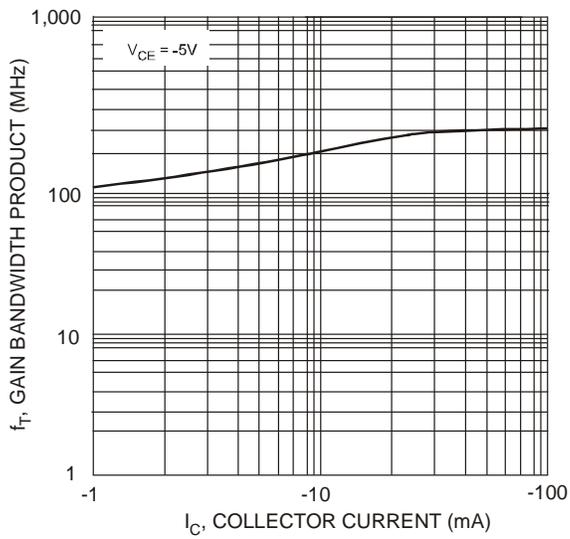
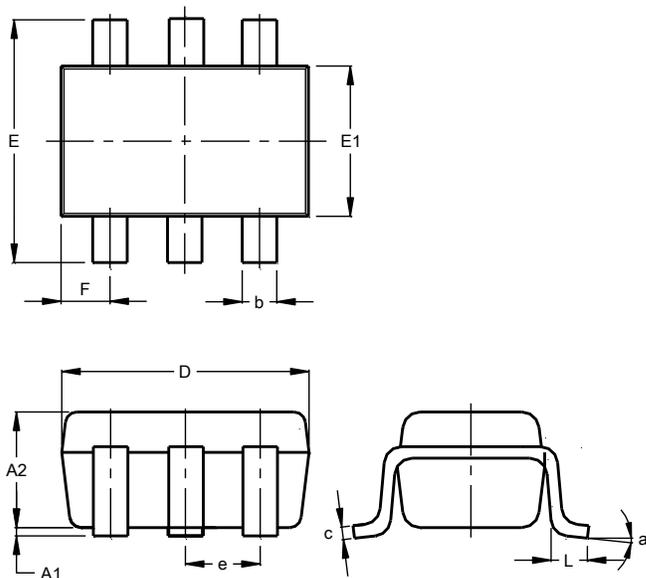


Fig. 7. Gain Bandwidth Product vs. Collector Current

Package Outline Dimensions

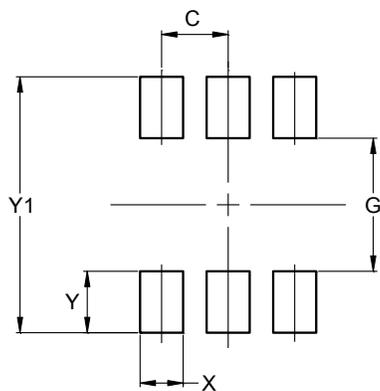
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500